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MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

Dual NPN Bias Resistor Transistors R1 = 22 kΩ, R2 = 22 kΩ

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q₁ and Q₂, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ORDERING INFORMATION

Device	Package	Shipping†
MUN5212DW1T1G, NSVMUN5212DW1T1G	SOT-363	3,000/Tape & Reel
NSBC124EDXV6T1G	SOT-563	4,000/Tape & Reel
NSBC124EDXV6T5G	SOT-563	8,000/Tape & Reel
NSBC124EDP6T5G	SOT-963	8,000/Tape & Reel

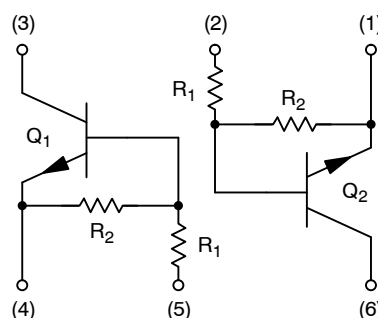
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



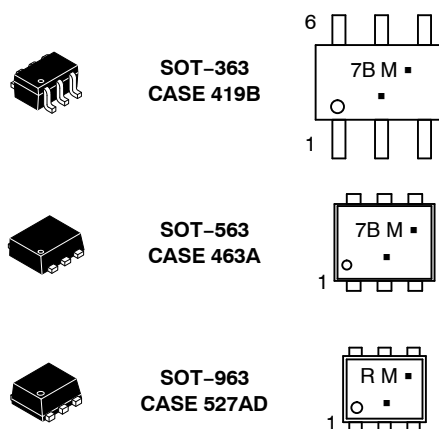
ON Semiconductor®

http://onsemi.com

PIN CONNECTIONS



MARKING DIAGRAMS



7B/R = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
MUN5212DW1 (SOT-363) ONE JUNCTION HEATED			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	187	mW
Derate above 25°C		256	$\text{mW}/^\circ\text{C}$
		1.5	
		2.0	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	670	$^\circ\text{C}/\text{W}$
		490	
MUN5212DW1 (SOT-363) BOTH JUNCTION HEATED (Note 3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	250	mW
Derate above 25°C		385	$\text{mW}/^\circ\text{C}$
		2.0	
		3.0	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	493	$^\circ\text{C}/\text{W}$
		325	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	188	$^\circ\text{C}/\text{W}$
		208	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
NSBC124EDXV6 (SOT-563) ONE JUNCTION HEATED			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	357	mW
Derate above 25°C		2.9	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
NSBC124EDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	500	mW
Derate above 25°C		4.0	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
NSBC124EDP6 (SOT-963) ONE JUNCTION HEATED			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	231	MW
Derate above 25°C		269	$\text{mW}/^\circ\text{C}$
		1.9	
		2.2	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
		464	
NSBC124EDP6 (SOT-963) BOTH JUNCTION HEATED (Note 3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	339	MW
Derate above 25°C		408	$\text{mW}/^\circ\text{C}$
		2.7	
		3.3	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	369	$^\circ\text{C}/\text{W}$
		306	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad.

2. FR-4 @ 1.0 × 1.0 Inch Pad.

3. Both junction heated values assume total power is sum of two equally powered channels.

 4. FR-4 @ 100 mm², 1 oz. copper traces, still air.

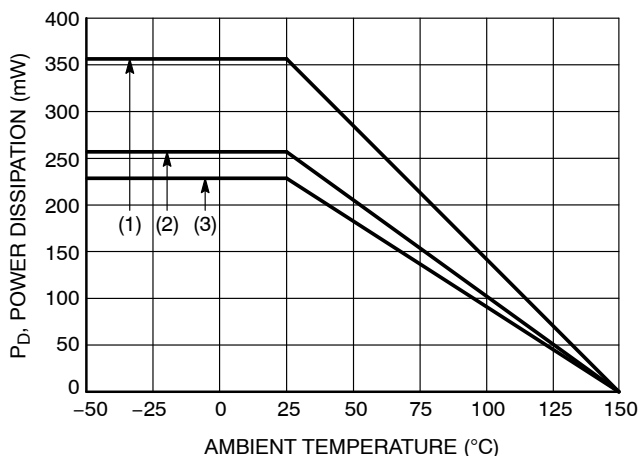
 5. FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, common for Q_1 and Q_2 , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	I_{CBO}	-	-	100	nA _{dc}
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$)	I_{CEO}	-	-	500	nA _{dc}
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	I_{EBO}	-	-	0.2	mA _{dc}
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	-	-	V _{dc}
Collector-Emitter Breakdown Voltage (Note 6) ($I_C = 2.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	-	-	V _{dc}
ON CHARACTERISTICS					
DC Current Gain (Note 6) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$)	h_{FE}	60	100	-	
Collector-Emitter Saturation Voltage (Note 6) ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	V
Input Voltage (Off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\ \mu\text{A}$)	$V_{i(off)}$	-	1.2	-	V _{dc}
Input Voltage (On) ($V_{CE} = 0.2\text{ V}$, $I_C = 5.0\text{ mA}$)	$V_{i(on)}$	-	1.9	-	V _{dc}
Output Voltage (On) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	V _{dc}
Output Voltage (Off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	V _{dc}
Input Resistor	R1	15.4	22	28.6	k Ω
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	

6. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle \leq 2%.



- (1) SOT-363; 1.0 x 1.0 Inch Pad
- (2) SOT-563; Minimum Pad
- (3) SOT-963; 100 mm², 1 oz. Copper Trace

Figure 1. Derating Curve

MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

**TYPICAL CHARACTERISTICS
 MUN5212DW1, NSBC124EDXV6**

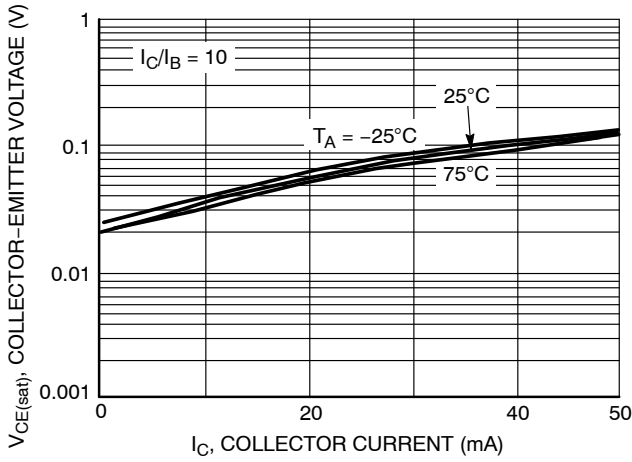


Figure 2. $V_{CE(sat)}$ vs. I_C

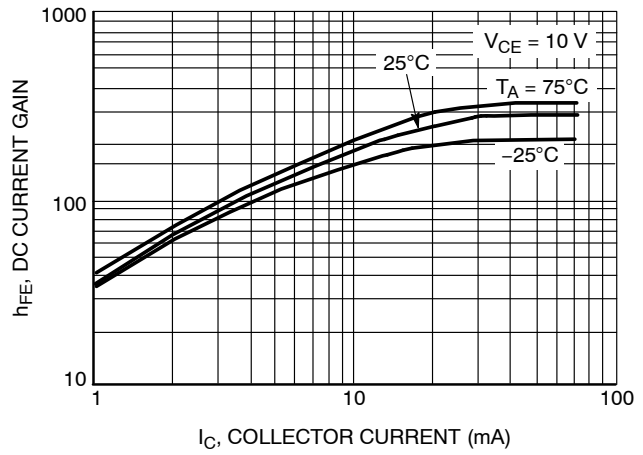


Figure 3. DC Current Gain

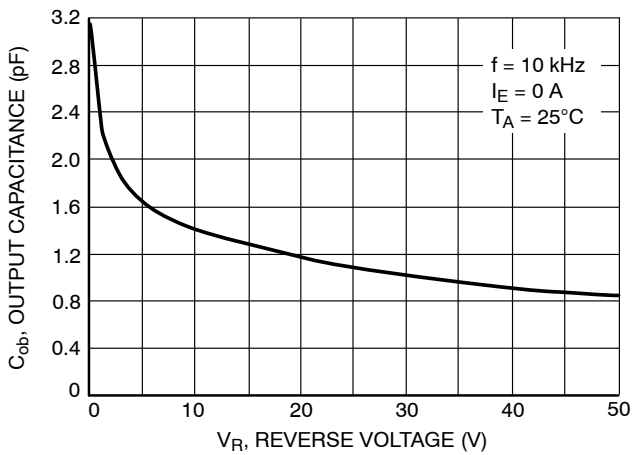


Figure 4. Output Capacitance

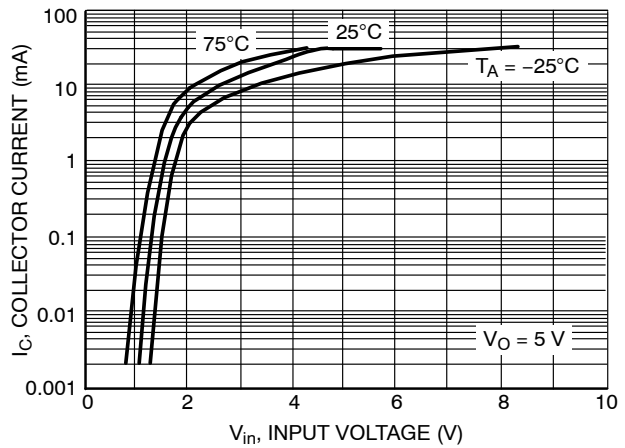


Figure 5. Output Current vs. Input Voltage

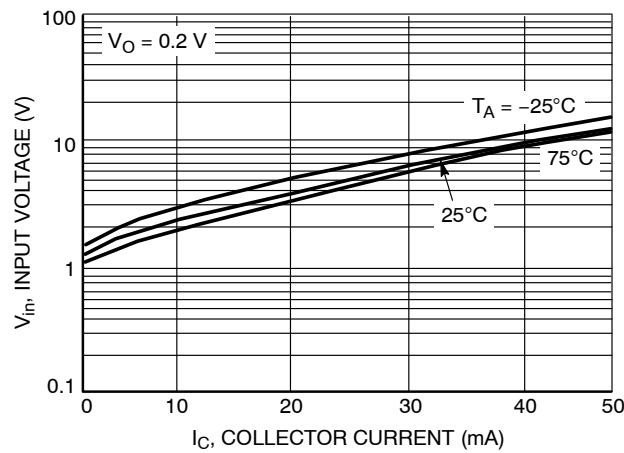


Figure 6. Input Voltage vs. Output Current

MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

**TYPICAL CHARACTERISTICS
 NSBC124EDP6**

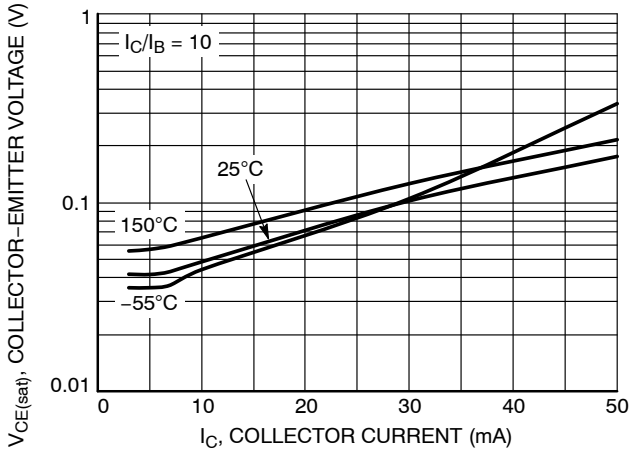


Figure 7. $V_{CE(sat)}$ vs. I_C

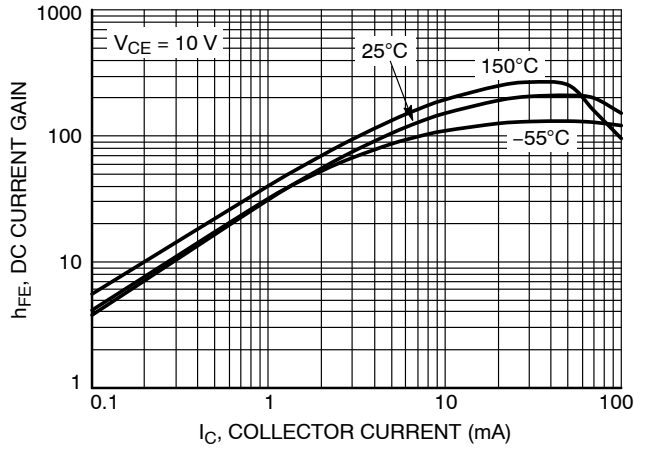


Figure 8. DC Current Gain

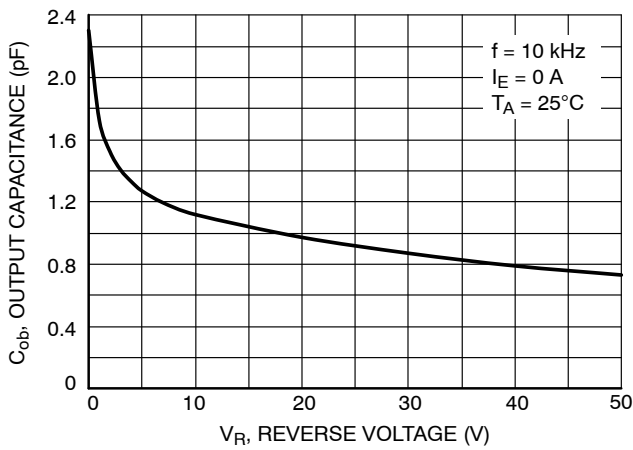


Figure 9. Output Capacitance

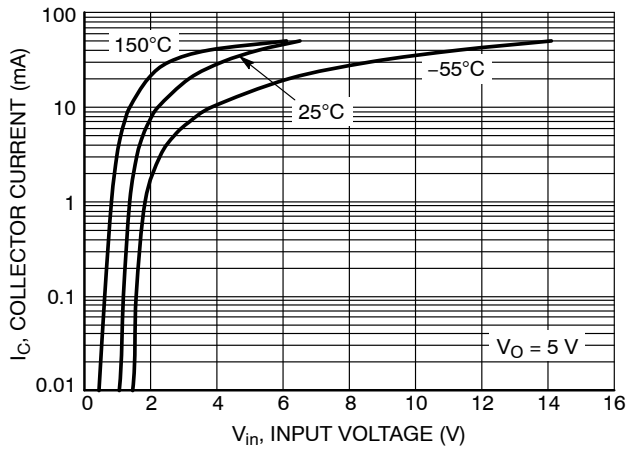


Figure 10. Output Current vs. Input Voltage

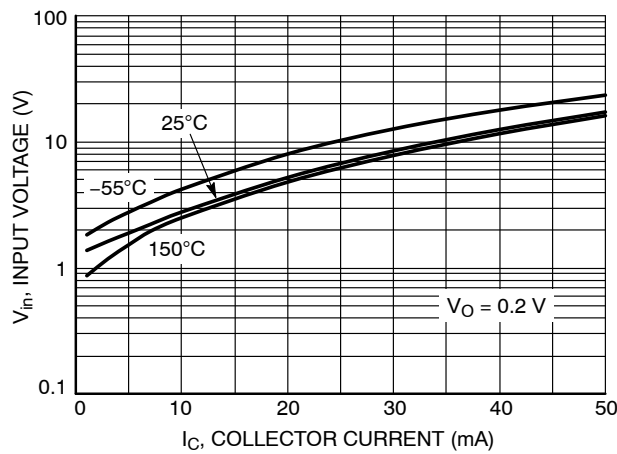


Figure 11. Input Voltage vs. Output Current

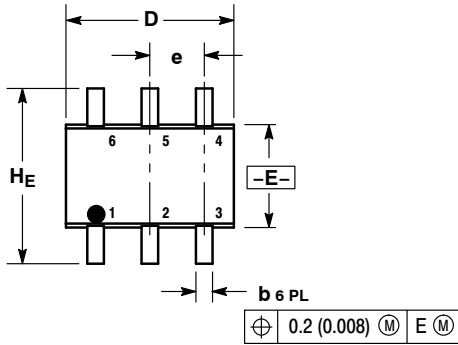
MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02

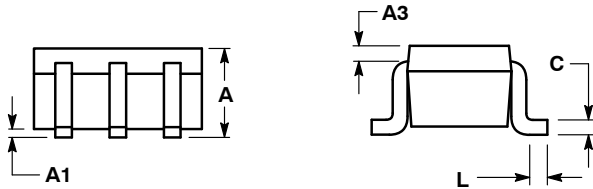
ISSUE W



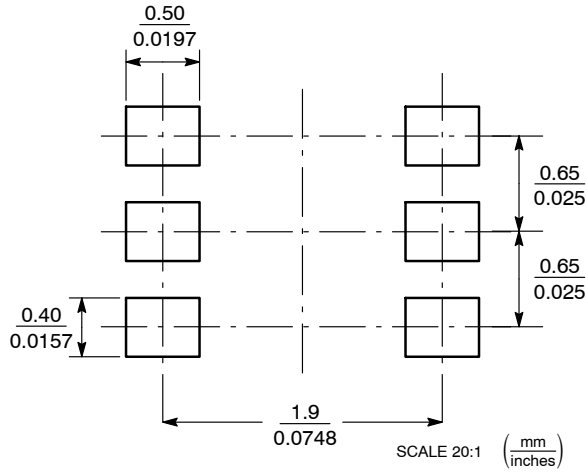
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086



SOLDERING FOOTPRINT*



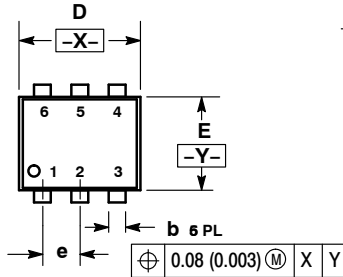
SC-88/SC70-6/SOT-363

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

PACKAGE DIMENSIONS

SOT-563, 6 LEAD
 CASE 463A
 ISSUE F

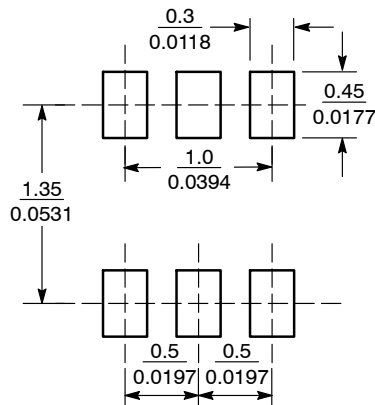


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



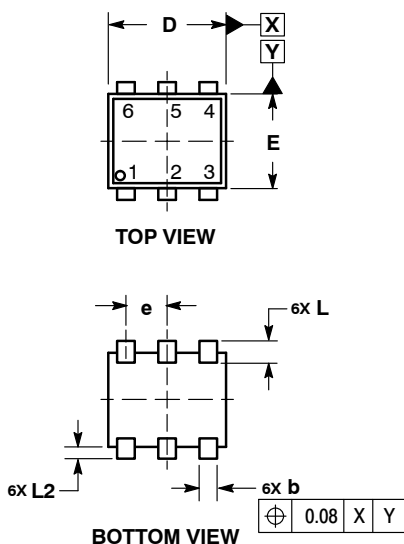
SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MUN5212DW1, NSBC124EDXV6, NSBC124EDP6

PACKAGE DIMENSIONS

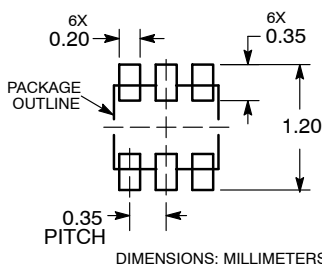
SOT-963 CASE 527AD ISSUE E



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H _E	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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